

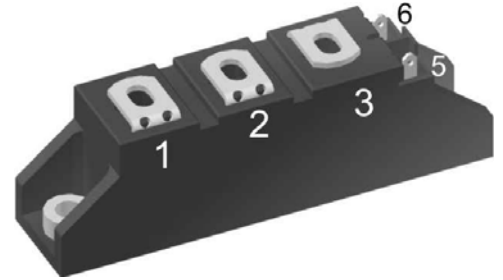
Thyristor Module

 $V_{RRM} = 2 \times 800V$
 $I_{TAV} = 27A$
 $V_T = 1.27V$

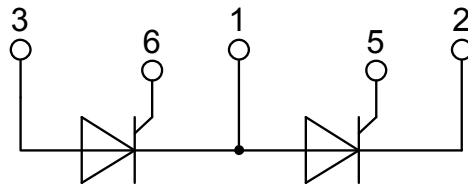
Phase leg

Part number

MCC26-08io8B



Backside: isolated



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

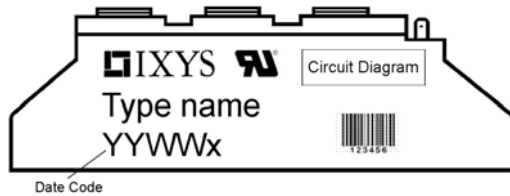
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

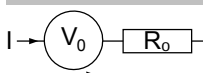
| Thyristor | | | | Ratings | | | |
|----------------|--|---|--------------------------|---------|------|-------------------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| $V_{RSM/DSM}$ | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 900 | V | |
| $V_{RRM/DRM}$ | max. repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 800 | V | |
| I_{RD} | reverse current, drain current | $V_{RD} = 800 V$ | $T_{VJ} = 25^{\circ}C$ | | 100 | μA | |
| | | $V_{RD} = 800 V$ | $T_{VJ} = 125^{\circ}C$ | | 3 | mA | |
| V_T | forward voltage drop | $I_T = 40 A$ | $T_{VJ} = 25^{\circ}C$ | | 1.27 | V | |
| | | $I_T = 80 A$ | | | 1.64 | V | |
| | | $I_T = 40 A$ | $T_{VJ} = 125^{\circ}C$ | | 1.27 | V | |
| | | $I_T = 80 A$ | | | 1.65 | V | |
| I_{TAV} | average forward current | $T_C = 85^{\circ}C$ | $T_{VJ} = 125^{\circ}C$ | | 27 | A | |
| $I_{T(RMS)}$ | RMS forward current | 180° sine | | | 50 | A | |
| V_{T0} | threshold voltage | } for power loss calculation only | $T_{VJ} = 125^{\circ}C$ | | 0.85 | V | |
| r_T | slope resistance | | | | 11 | m Ω | |
| R_{thJC} | thermal resistance junction to case | | | | 0.88 | K/W | |
| R_{thCH} | thermal resistance case to heatsink | | | 0.20 | | K/W | |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 115 | W | |
| I_{TSM} | max. forward surge current | t = 10 ms; (50 Hz), sine | $T_{VJ} = 45^{\circ}C$ | | 520 | A | |
| | | t = 8,3 ms; (60 Hz), sine | $V_R = 0 V$ | | 560 | A | |
| | | t = 10 ms; (50 Hz), sine | $T_{VJ} = 125^{\circ}C$ | | 440 | A | |
| | | t = 8,3 ms; (60 Hz), sine | $V_R = 0 V$ | | 475 | A | |
| I^2t | value for fusing | t = 10 ms; (50 Hz), sine | $T_{VJ} = 45^{\circ}C$ | | 1.35 | kA ² s | |
| | | t = 8,3 ms; (60 Hz), sine | $V_R = 0 V$ | | 1.31 | kA ² s | |
| | | t = 10 ms; (50 Hz), sine | $T_{VJ} = 125^{\circ}C$ | | 970 | A ² s | |
| | | t = 8,3 ms; (60 Hz), sine | $V_R = 0 V$ | | 940 | A ² s | |
| C_J | junction capacitance | $V_R = 400 V$ f = 1 MHz | $T_{VJ} = 25^{\circ}C$ | | 22 | pF | |
| P_{GM} | max. gate power dissipation | $t_p = 30 \mu s$ | $T_C = 125^{\circ}C$ | | 10 | W | |
| | | $t_p = 300 \mu s$ | | | 5 | W | |
| P_{GAV} | average gate power dissipation | | | | 0.5 | W | |
| $(di/dt)_{cr}$ | critical rate of rise of current | $T_{VJ} = 125^{\circ}C$; f = 50 Hz | repetitive, $I_T = 45 A$ | | 150 | A/ μs | |
| | | $t_p = 200 \mu s$; $di_G/dt = 0.45 A/\mu s$; $I_G = 0.45 A$; $V_D = \frac{2}{3} V_{DRM}$ | non-repet., $I_T = 27 A$ | | 500 | A/ μs | |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage | $V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise) | $T_{VJ} = 125^{\circ}C$ | | 1000 | V/ μs | |
| V_{GT} | gate trigger voltage | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 1.5 | V | |
| | | | $T_{VJ} = -40^{\circ}C$ | | 1.6 | V | |
| I_{GT} | gate trigger current | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 100 | mA | |
| | | | $T_{VJ} = -40^{\circ}C$ | | 200 | mA | |
| V_{GD} | gate non-trigger voltage | $V_D = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 125^{\circ}C$ | | 0.2 | V | |
| I_{GD} | gate non-trigger current | | | | 10 | mA | |
| I_L | latching current | $t_p = 10 \mu s$ | $T_{VJ} = 25^{\circ}C$ | | 450 | mA | |
| | | $I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$ | | | | | |
| I_H | holding current | $V_D = 6 V$ $R_{GK} = \infty$ | $T_{VJ} = 25^{\circ}C$ | | 200 | mA | |
| t_{gd} | gate controlled delay time | $V_D = \frac{1}{2} V_{DRM}$ | $T_{VJ} = 25^{\circ}C$ | | 2 | μs | |
| | | $I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$ | | | | | |
| t_q | turn-off time | $V_R = 100 V$; $I_T = 20 A$; $V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s$; $dv/dt = 20 V/\mu s$; $t_p = 200 \mu s$ | $T_{VJ} = 125^{\circ}C$ | | 150 | μs | |

| Package TO-240AA | | | | Ratings | | |
|------------------|--|----------------------|-------------------------------------|---------|------|------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal | | | 200 | A |
| T_{VJ} | virtual junction temperature | | -40 | | 125 | °C |
| T_{op} | operation temperature | | -40 | | 100 | °C |
| T_{stg} | storage temperature | | -40 | | 125 | °C |
| Weight | | | | | 90 | g |
| M_D | mounting torque | | 2.5 | | 4 | Nm |
| M_T | terminal torque | | 2.5 | | 4 | Nm |
| $d_{Spp/App}$ | creepage distance on surface striking distance through air | terminal to terminal | 13.0 | 9.7 | | mm |
| $d_{Spb/Apb}$ | | terminal to backside | 16.0 | 16.0 | | mm |
| V_{ISOL} | isolation voltage | t = 1 second | | 3600 | | V |
| | | t = 1 minute | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 3000 | | V |

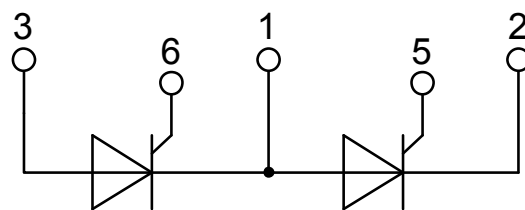
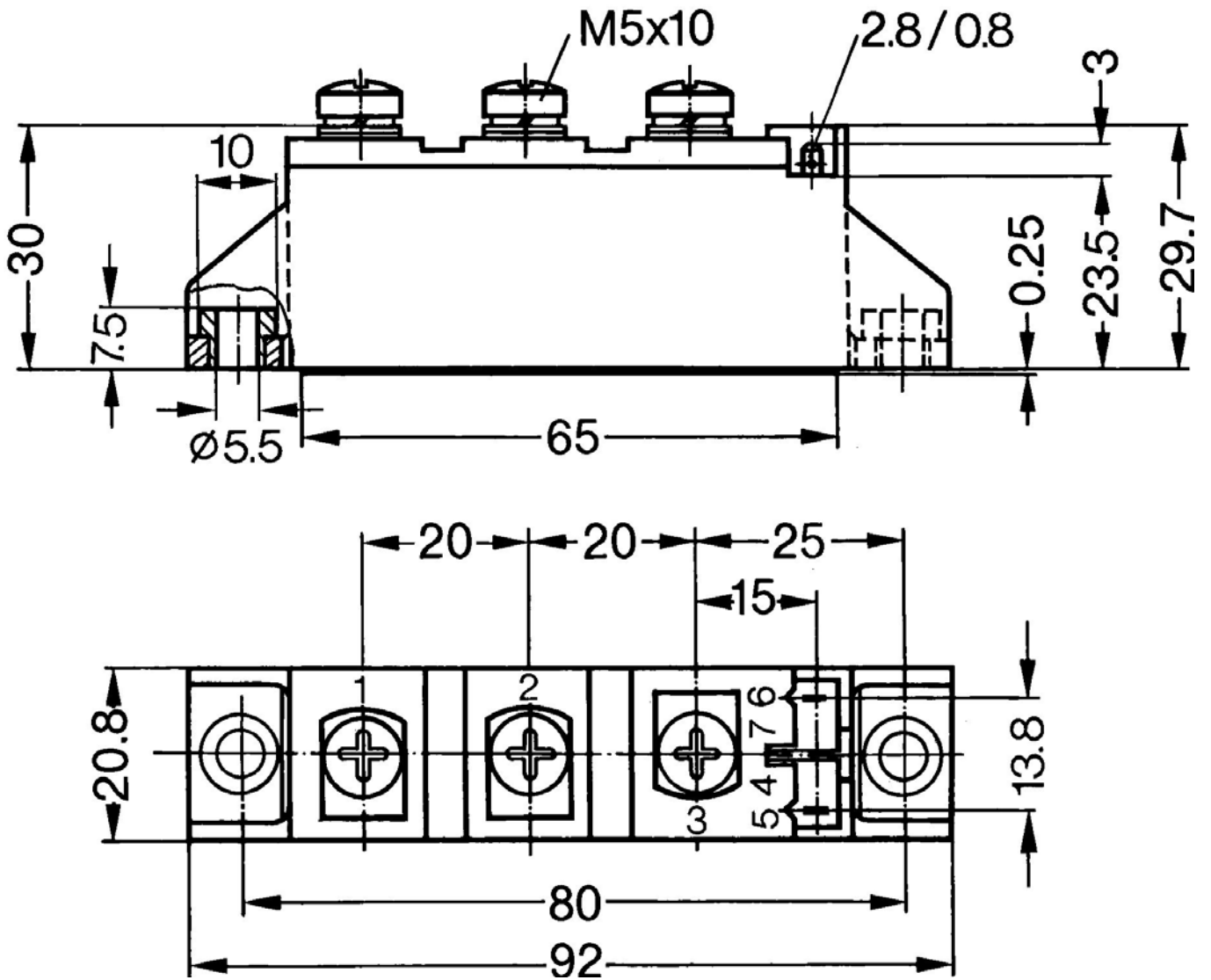


| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|--------------|--------------------|---------------|----------|----------|
| Standard | MCC26-08io8B | MCC26-08io8B | Box | 6 | 457752 |

| Similar Part | Package | Voltage class |
|---------------|-------------|---------------|
| MCMA35P1200TA | TO-240AA-1B | 1200 |
| MCMA50P1200TA | TO-240AA-1B | 1200 |

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 125\text{ °C}$

Thyristor

| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.85 | V |
| $R_{0\ max}$ | slope resistance * | 9.8 | mΩ |



Thyristor

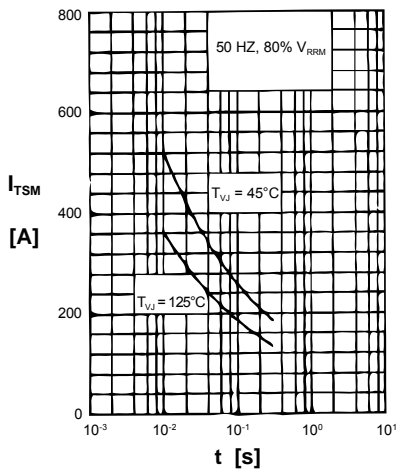


Fig. 1 Surge overload current
 I_{TSM} : Crest value, t : duration

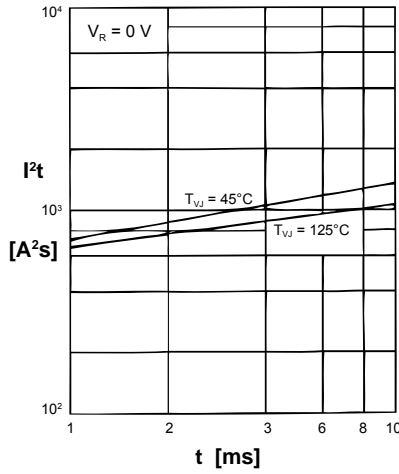


Fig. 2 I^2t versus time (1-10 ms)

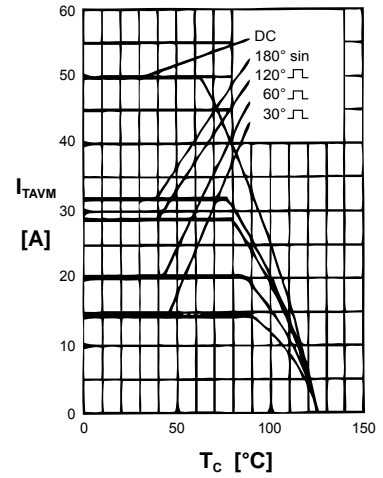


Fig. 3 Max. forward current at case temperature

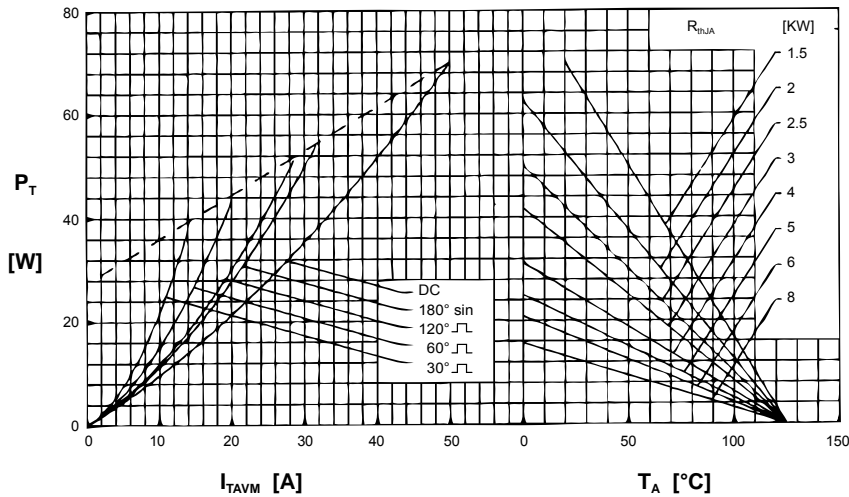


Fig. 4 Power dissipation versus onstate current & ambient temp. (per thyristor)

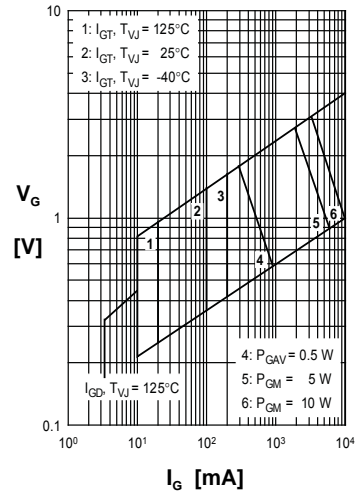


Fig. 5 Gate trigger charact.

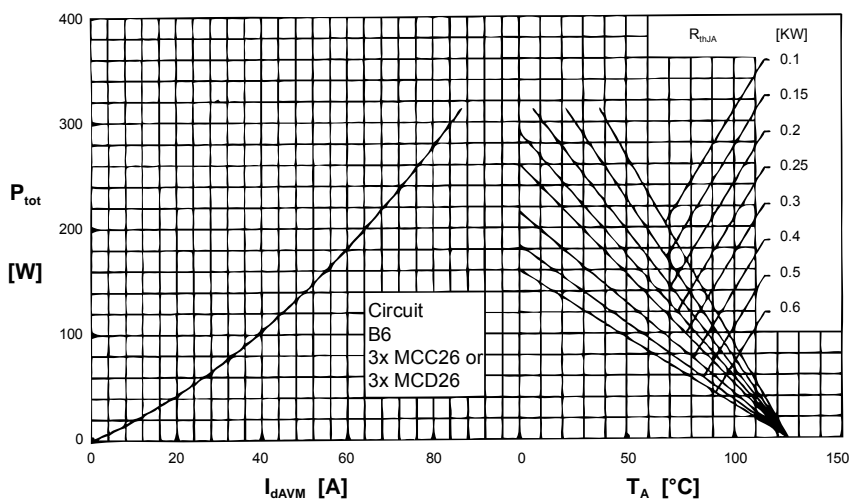


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

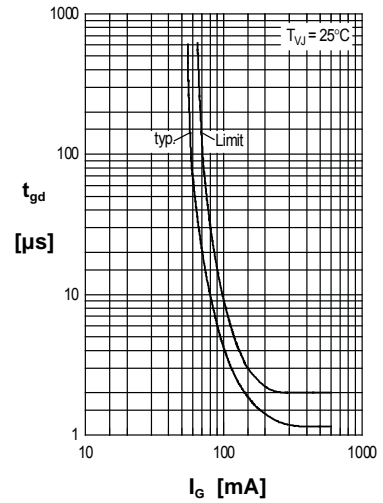


Fig. 7 Gate trigger delay time

Thyristor

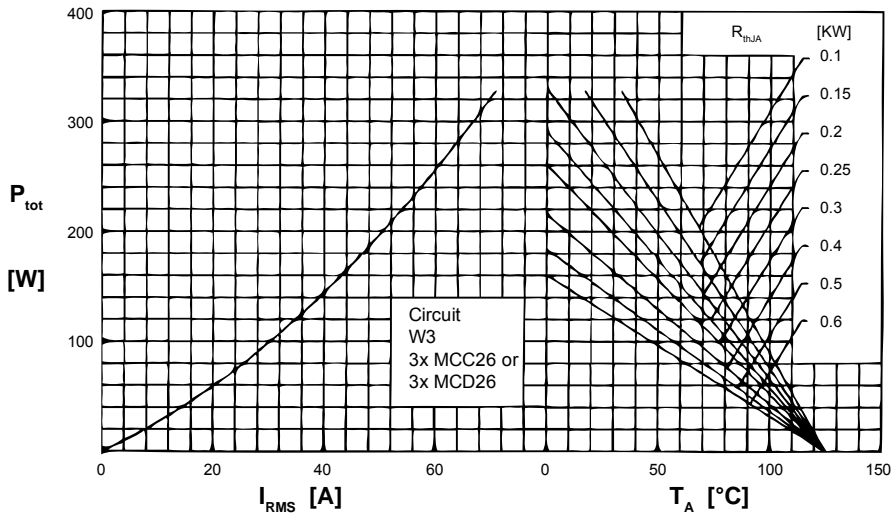


Fig. 8 Three phase AC-controller: Power dissipation vs. RMS output current and ambient temperature

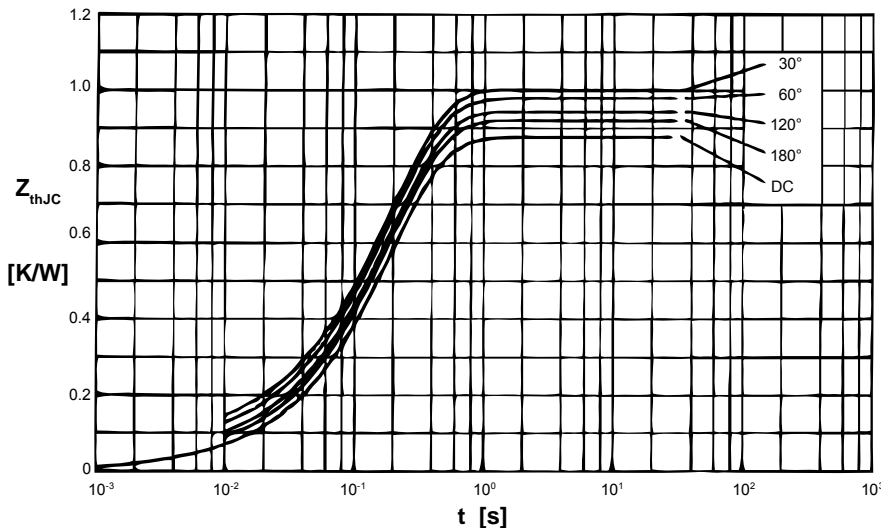


Fig. 9 Transient thermal impedance junction to case (per thyristor)

R_{thJC} for various conduction angles d :

| d | R_{thJC} [K/W] |
|------|------------------|
| DC | 0.88 |
| 180° | 0.92 |
| 120° | 0.95 |
| 60° | 0.98 |
| 30° | 1.01 |

Constants for Z_{thJC} calculation:

| i | R_{thi} [K/W] | t_i [s] |
|-----|-----------------|-----------|
| 1 | 0.019 | 0.0031 |
| 2 | 0.029 | 0.0216 |
| 3 | 0.832 | 0.1910 |

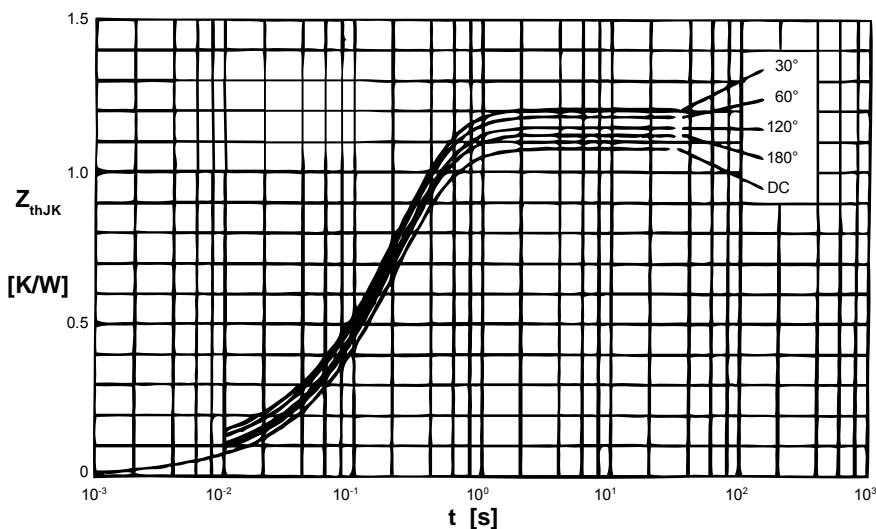


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

R_{thJK} for various conduction angles d :

| d | R_{thJK} [K/W] |
|------|------------------|
| DC | 1.08 |
| 180° | 1.12 |
| 120° | 1.15 |
| 60° | 1.18 |
| 30° | 1.21 |

Constants for Z_{thJK} calculation:

| i | R_{thi} [K/W] | t_i [s] |
|-----|-----------------|-----------|
| 1 | 0.019 | 0.0031 |
| 2 | 0.029 | 0.0216 |
| 3 | 0.832 | 0.1910 |
| 4 | 0.200 | 0.4500 |